CLAIMS

[Claim 1]

A semiconductor processing sheet comprising ~~an~~ a pressure-sensitive adhesive layer on a base material, wherein

the pressure-sensitive adhesive layer comprises an adhesive resin (i) and a crosslinking agent (ii),

a content of the crosslinking agent (ii) in the pressure-sensitive adhesive layer is 10 to 50 parts by mass with respect to 100 parts by mass of the adhesive resin (i), and

the semiconductor processing sheet has a following characteristics:

when a thickness of the pressure-sensitive adhesive layer is 200 μm, a storage elastic modulus of the pressure-sensitive adhesive layer having a thickness of 200 μm at 0°C is equal to or less than 1,000 MPa; and

when the semiconductor processing sheet is adhered to a mirror surface of a semiconductor wafer, an adhesive force of the pressure-sensitive adhesive layer with respect to the mirror surface is equal to or less than 200 mN / 25 mm.

[Claim 2]

A semiconductor processing sheet comprising one pressure-sensitive adhesive layer on a base material, wherein

the semiconductor processing sheet has a following characteristics:

when a thickness of the pressure-sensitive adhesive layer is 200 μm, a storage elastic modulus of the pressure-sensitive adhesive layer having a thickness of 200 μm at 0°C is equal to or less than 1,000 MPa; and

when the semiconductor processing sheet is adhered to a mirror surface of a

semiconductor wafer, an adhesive force of the pressure-sensitive adhesive layer with respect to the mirror surface is equal to or less than 200 mN / 25 mm.

[Claim 3]

The semiconductor processing sheet according to Claim 1 or 2, wherein the pressure-sensitive adhesive layer is non-energy ray-curable.

[Claim 4]

The semiconductor processing sheet according to any one of Claims 1 to 3, further comprising a film adhesive on the pressure-sensitive adhesive layer.